

Device Modeling Report

COMPONENTS: Light-Emitting Diode (LED) STANDARD
PART NUMBER: OSWT5161A
MANUFACTURER: OPTO SUPPLY
REMARK: TA=60 degree C

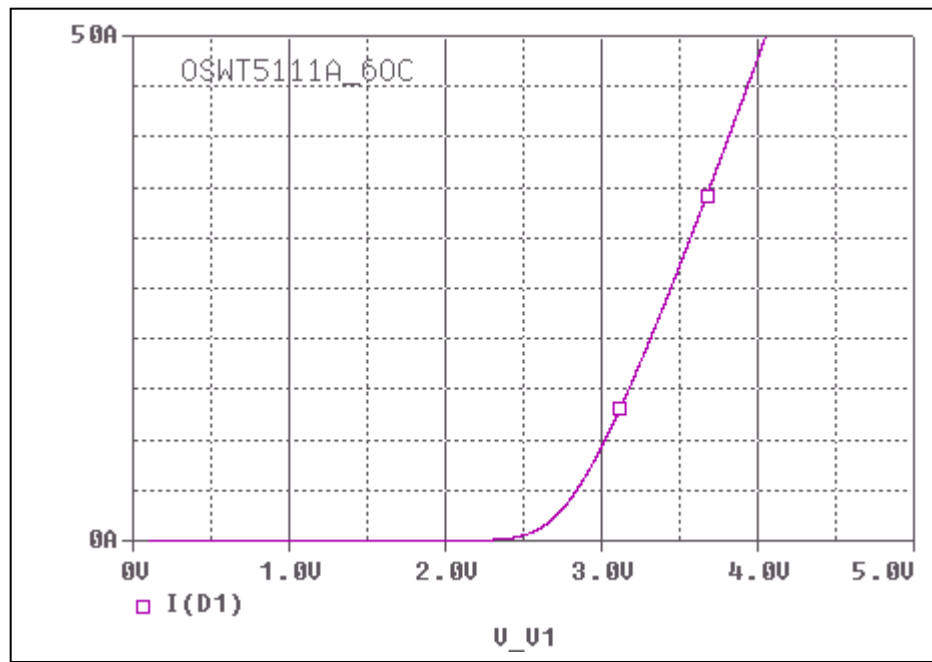


Bee Technologies Inc.

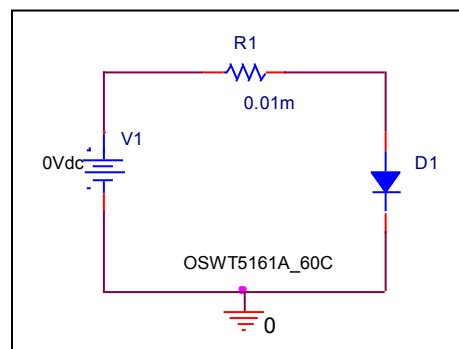
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

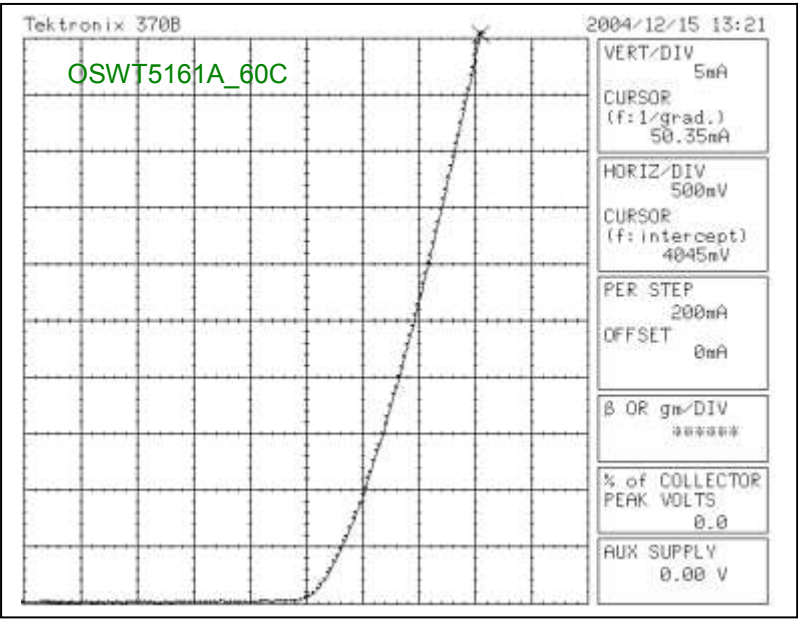


Evaluation Circuit



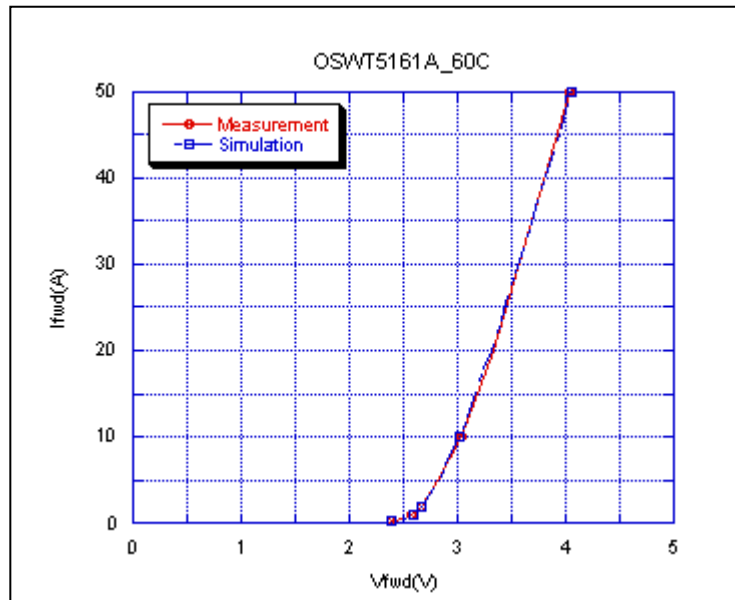
Forward Current Characteristic

Reference



Comparison Graph

Circuit Simulation Result

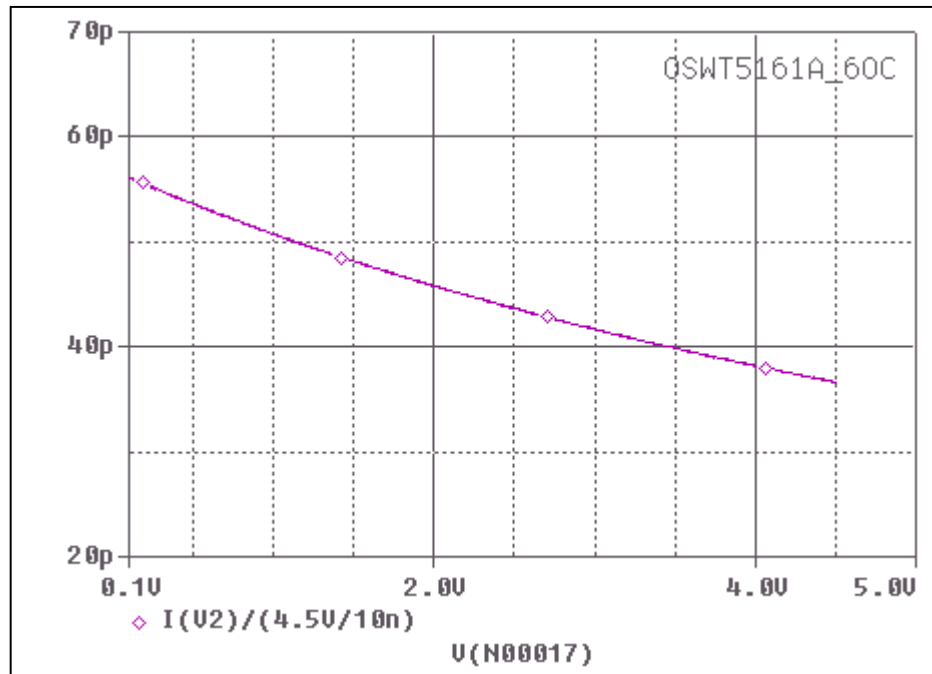


Simulation Result

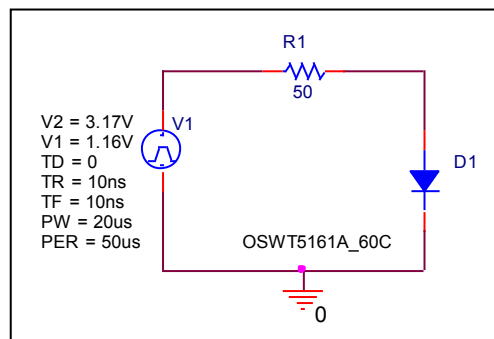
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.2	2.385	2.387	0.0838
0.5	2.505	2.492	0.5189
1	2.575	2.585	0.3883
2	2.675	2.676	0.0373
5	2.815	2.84	0.8880
10	3.03	3.025	0.1650
20	3.33	3.312	0.5405
50	4.045	4.05	0.1236

Capacitance Characteristic

Circuit Simulation Result

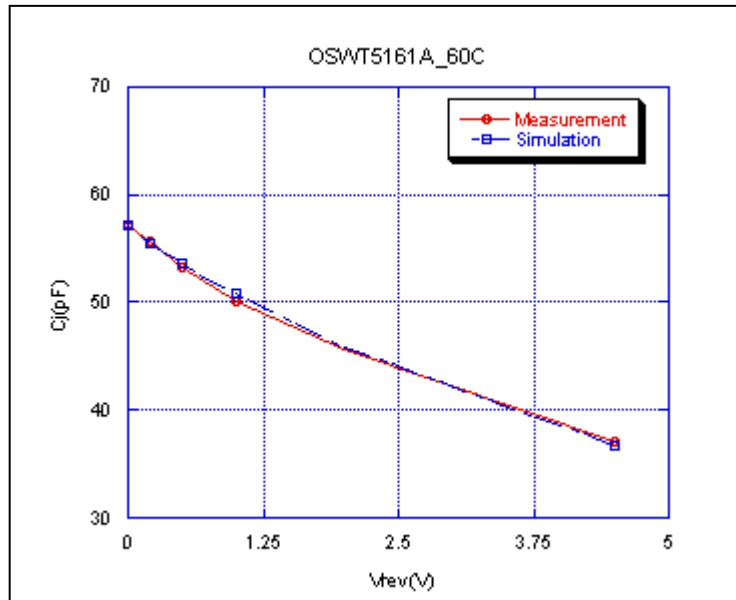


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

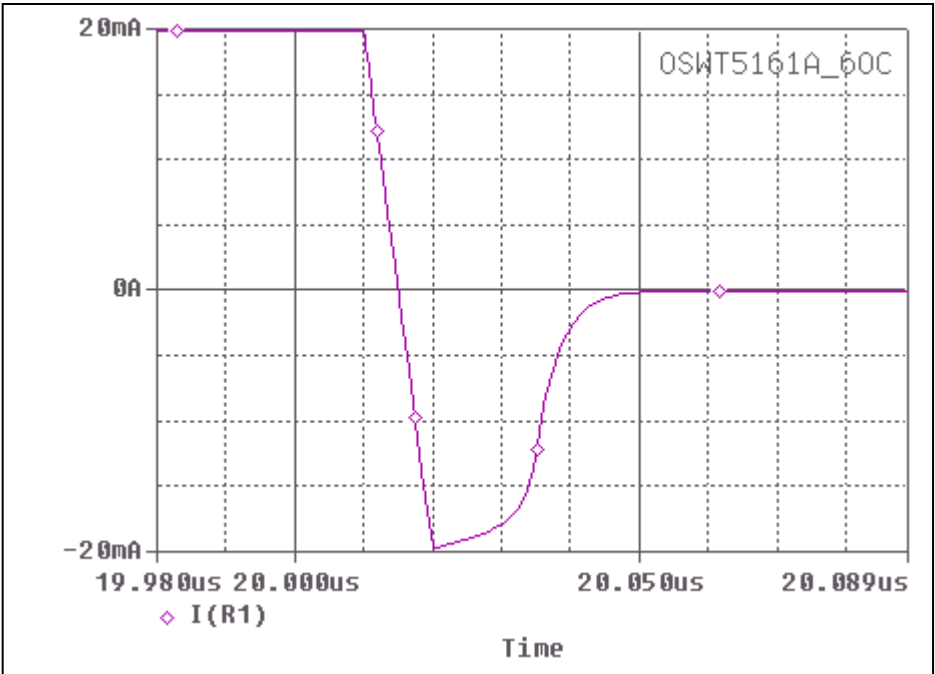


Simulation Result

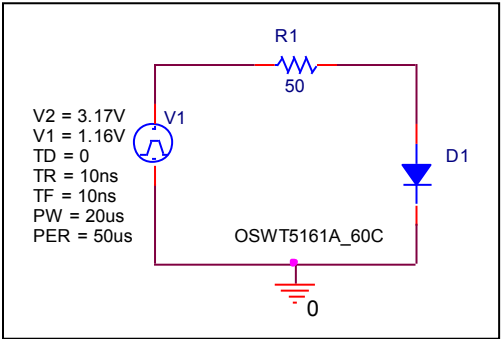
V_{rev} (V)	Cj(pF) Measurement	Cj(pF) Simulation	%Error
0	57.1	57.1	0
0.1	56.4	56.156	0.4326
0.2	55.69	55.501	0.3393
0.5	53.265	53.65	0.7228
1	50	50.77	1.54
2	45.7	45.83	0.2844
4.5	37	36.7	0.8108

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

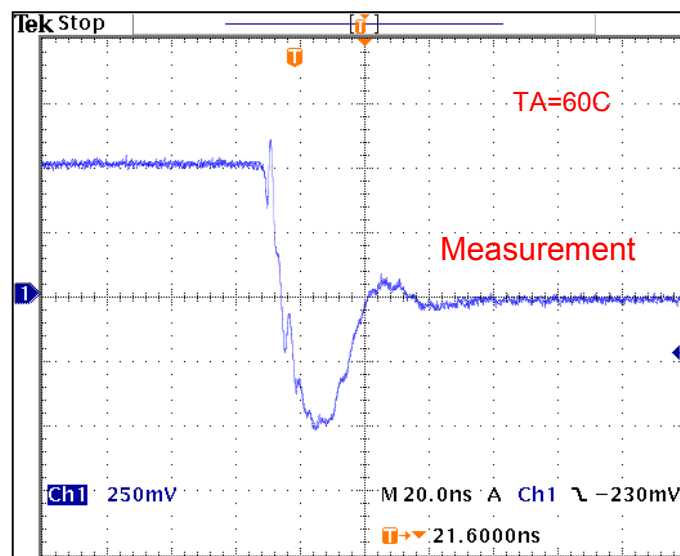


Compare Measurement vs. Simulation

Symbol	Measurement	Unit	Simulation	Unit	%Error
$T_{rr}=t_{rj}+t_{rb}$	25.6	ns	25.68	ns	0.312

Reverse Recovery Characteristic

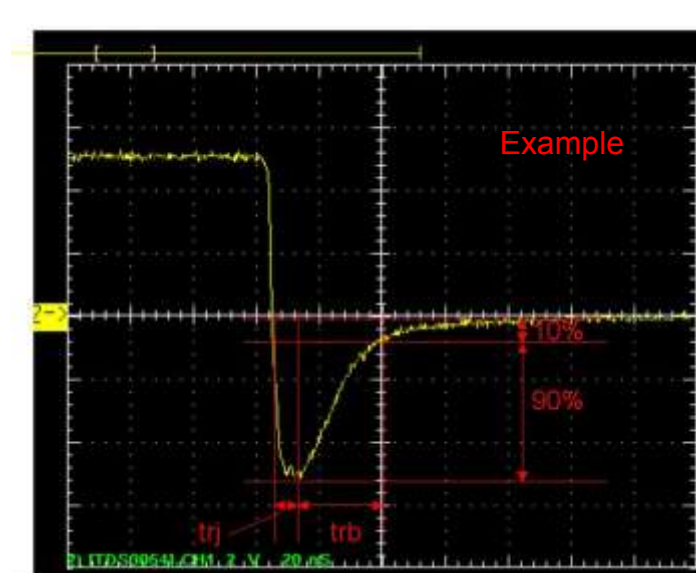
Reference



$T_{rj} = 10.4(\text{ns})$

$T_{rb} = 15.2(\text{ns})$

Conditions: $I_{fwd} = I_{rev} = 0.02(\text{A})$, $R_I = 50$



Relation between t_{rj} and t_{rb}